VS-ST780CL Series

Vishay Semiconductors



Phase Control Thyristors (Hockey PUK Version), 1350 A



B-PUK (TO-200AC)

PRIMARY CHARACTERISTICS								
I _{T(AV)} 1350 A								
V _{DRM} /V _{RRM}	400 V, 600 V							
V _{TM}	1.31 V							
I _{GT}	100 mA							
TJ	-40 °C to +125 °C							
Package	B-PUK (TO-200AC)							
Circuit configuration	Single SCR							

FEATURES

- · Center amplifying gate
- · Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC)
- Designed and qualified for industrial level
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
1		1350	A					
I _{T(AV)}	T _{hs}	55	O°					
laura and		2700	A					
I _T (RMS)	T _{hs}	25	O°					
1	50 Hz	24 400	A					
ITSM	60 Hz	25 600	A					
l ² t	50 Hz	2986	kA ² s					
141	60 Hz	2726	KA-S					
V _{DRM} /V _{RRM}		400 to 600	V					
t _q	Typical	150	μs					
TJ		-40 to 125	O°					

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS										
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA						
VS-ST780CL	04	400	500	80						
V3-31780CL	06	600	700	00						

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COMPLIANT

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ABSOLUTE MAXIMUM RATING	5						
PARAMETER	SYMBOL		TEST CON	DITIONS	VALUES	UNITS	
Maximum average on-state current	1	180° conduction, half sine wave		1350 (500)	А		
at heatsink temperature	I _{T(AV)}	double side	(single side) co	oled	55 (85)	°C	
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	C heatsink tempe	erature double side cooled	2700		
		t = 10 ms	No voltage		24 400		
Maximum peak, one-cycle non-repetitive surge current	l	t = 8.3 ms	reapplied		25 600	А	
	I _{TSM}	t = 10 ms	100 % V _{RBM}	Sinusoidal half wave, initial T _J = T _J maximum	20 550		
		t = 8.3 ms	reapplied		21 500		
Maximum I ² t for fusing		t = 10 ms	No voltage reapplied 100 % V _{BBM}		2986	kA ² s	
	l ² t	t = 8.3 ms			2726		
Maximum -t for fusing	1-1	t = 10 ms			2112		
		t = 8.3 ms	reapplied		1928		
Maximum I ² √t for fusing	l²√t	t = 0.1 to 10) ms, no voltage	reapplied	29 860	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$\times I_{T(AV)} < I < \pi \times I_{T(AV)}$	I _{T(AV)}), T _J = T _J maximum	0.80	v	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$				
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), T _J = T _J maximum			0.14	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			0.13	11152	
Maximum on-state voltage	V _{TM}	$I_{pk} = 3600 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$			1.31	V	
Maximum holding current	Ι _Η	T 25 °C	anodo supply 1	2 V resistive load	600	mA	
Typical latching current	١L	$1_{\rm J} = 25$ C,	anoue supply 1		1000	ma	

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega, t_r \! \leq \! 1 \; \mu s$ $T_J = T_J$ maximum, anode voltage $\leq \! 80 \; \% \; V_{DRM}$	1000	A/μs				
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C	1.0					
Typical turn-off time	tq	I_{TM} = 750 A, T_J = T_J maximum, dl/dt = 60 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	150	μs				

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	80	mA





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TRIGGERING							
PARAMETER	SYMBOL	тес	VAL	UNITS			
PANAMEIEN	TES	TEST CONDITIONS					
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum,	t _p ≤5 ms	10	0.0	w	
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv	
Maximum peak positive gate current	I _{GM}	$T_{\rm J} = T_{\rm J}$ maximum,	t _p ≤5 ms	3	.0	А	
Maximum peak positive gate voltage	+ V _{GM}		T. T. manimum A. 45 mm			V	
Maximum peak negative gate voltage	- V _{GM}	ij = ij maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms]	
		T _J = -40 °C		200	-		
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate	100	200	mA	
		T _J = 125 °C	trigger/current/voltage are the lowest value which will trigger	50	-		
		T _J = -40 °C	all units 12 V anode to cathode	2.5	-		
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	applied	1.8	3.0	V	
		T _J = 125 °C		1.1	-		
DC gate current not to trigger	I _{GD}		Maximum gate	10		mA	
DC gate voltage not to trigger	V _{GD}	T _J = T _J maximum	current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode	0.	25	V	

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum operating junction temperature range	TJ		-40 to 125	O			
Maximum storage temperature range	T _{Stg}		-40 to 150	- °C			
Movimum thermal registeres, junction to be stainly	Р	DC operation single side cooled	0.073				
Maximum thermal resistance, junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.031	к/w			
Maximum thermal resistance, case to heatsink	P	DC operation single side cooled	0.011				
	R _{thC-hs}	DC operation double side cooled	0.006				
Mounting force, ± 10 %			14 700 (1500)	N (kg)			
Approximate weight			255	g			
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-2	200AC)			

CONDUCTION ANGLE	SINUSOIDAL	CONDUCTION	RECTANGULAR	R CONDUCTION	TEST CONDITIONS	UNITS			
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS			
180°	0.009	0.009	0.006	0.006					
120°	0.011	0.011	0.011	0.011		K/W			
90°	0.014	0.014	0.015	0.015	$T_J = T_J maximum$				
60°	0.020	0.020	0.021	0.021					
30°	0.036	0.036	0.036	0.036					

Note

• The table above shows the increment of thermal resistance RthJ-hs when devices operate at different conduction angles than DC

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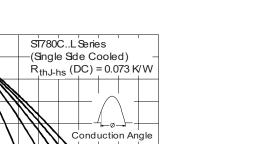


130

120

110

100



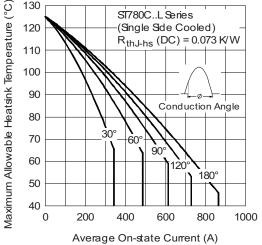
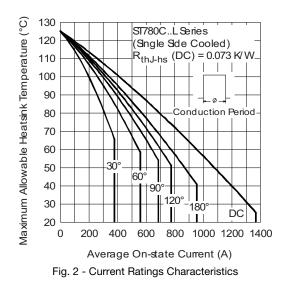
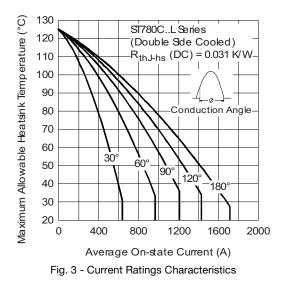


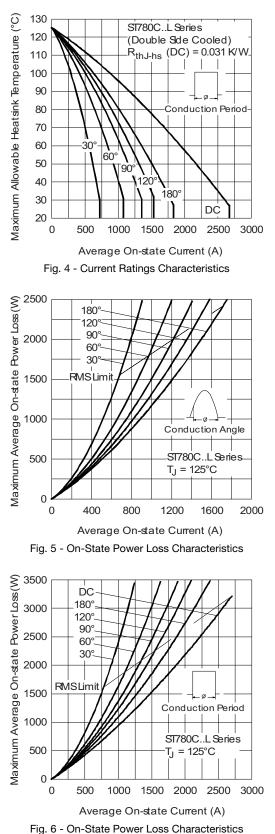
Fig. 1 - Current Ratings Characteristics







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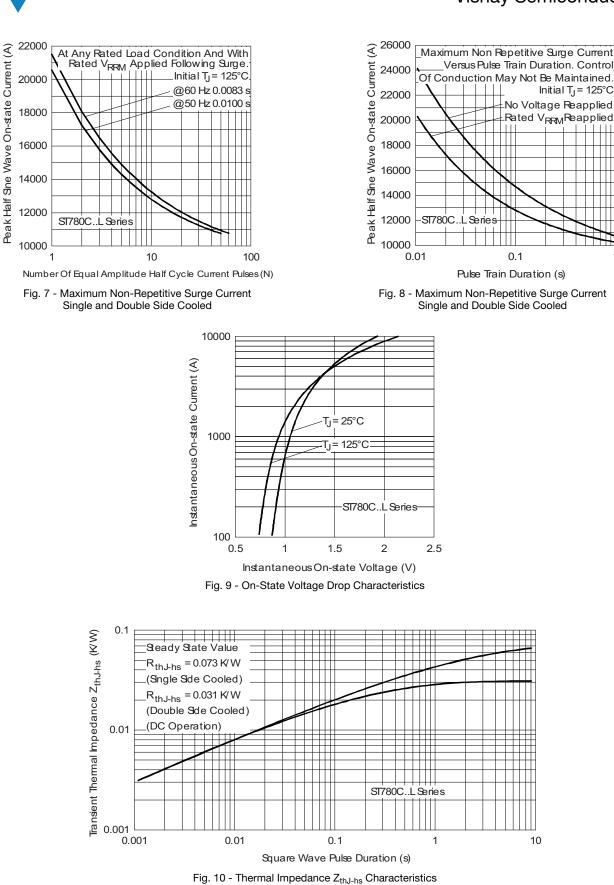
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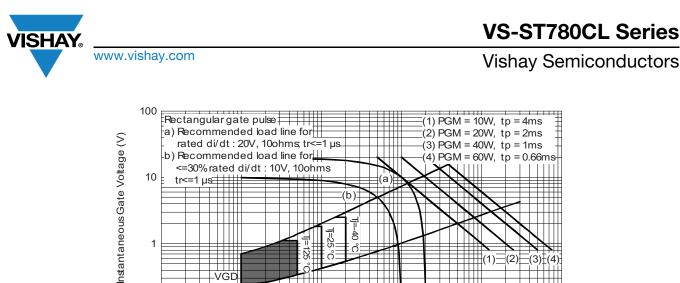
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Device: ST780C..L Series

Fig. 11 - Gate Characteristics

0.1

Frequency Limited by PG(AV)

1

Instantaneous Gate Current (A)

10

100

IGD

0.01

Ш

0.1 0.001

ORDERING INFORMATION TABLE

Device code	VS-	ST	78	0	С	06	L	1	-
		(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)
	1 -	· Visł	nay Serr	nicondu	ctors pr	oduct	C	C	
	2 -	Thy	ristor						
	3 -	Ess	ential pa	art numl	oer				
	4 -	0 =	convert	er grade	Ð				
	5 -	C =	cerami	c PUK					
	6 -	Volt	age coo	de x 100	$0 = V_{RRN}$	1 (see V	oltage F	Ratings	table)
	7 -	L=	PUK ca	se B-Pl	JK (TO-:	200AC)			
	8 -	0 =	eyelet t	erminals	s (gate a	ind aux	iliary ca	thode u	nsolder
		1 =	fast-on	termina	ls (gate	and aux	xiliary ca	athode	unsolde
	9 -	Crit	ical dV/	dt: • No	ne = 50	0 V/µs (standar	d selec	tion)
				• L =	= 1000 V	∕/µs (sp	ecial sel	lection)	

LINKS TO RELATED DOCUMENTS					
Dimensions	http://www.vishay.com/doc?95076				

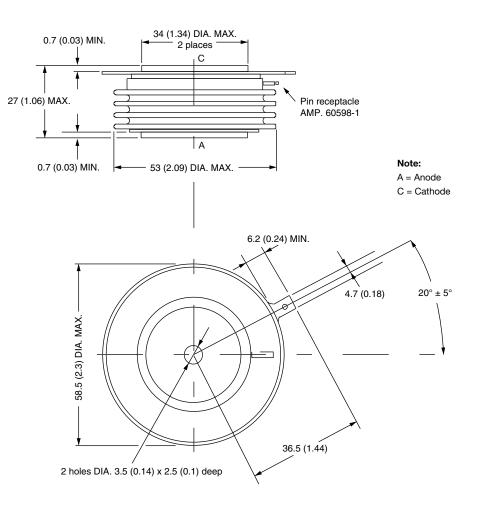
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B-PUK (TO-200AC)

DIMENSIONS in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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